

Substitute for Form 1449 A & B/PTO				<i>Complete if Known</i>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <i>(use as many sheets as necessary)</i>				Application Number	10/519,084
				Confirmation Number	7332
				Filing Date	December 23, 2004
				First Named Inventor	Heiji WATANABE
				Art Unit	2822
				Examiner Name	Tsz K. CHIU
Sheet	1	of	1	Attorney Docket Number	O85504

## **U.S. PATENT DOCUMENTS**

## **FOREIGN PATENT DOCUMENTS**

## **NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation <sup>6</sup>
/TC/		H.-J. Cho, et al.: "Novel Nitrogen Profile Engineering for Improved TaN/HfO <sub>2</sub> /Si MOSFET Performance"; IEDM, Technical Digest 2001, pages 655-658	

<b>Examiner Signature</b>	Tsz Chiu / (06/11/2007)	<b>Date Considered</b>	06/11/2007
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				<p><i>Complete if Known</i></p> <table border="1"> <tr> <td>Application Number</td> <td>10/519,084</td> </tr> <tr> <td>Confirmation Number</td> <td>7332</td> </tr> <tr> <td>Filing Date</td> <td>December 23, 2004</td> </tr> <tr> <td>First Named Inventor</td> <td>Heiji WATANABE</td> </tr> <tr> <td>Art Unit</td> <td>2812 2822</td> </tr> <tr> <td>Examiner Name</td> <td>Not Yet Assigned</td> </tr> <tr> <td colspan="2">Attorney Docket Number</td> </tr> </table>		Application Number	10/519,084	Confirmation Number	7332	Filing Date	December 23, 2004	First Named Inventor	Heiji WATANABE	Art Unit	2812 2822	Examiner Name	Not Yet Assigned	Attorney Docket Number	
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/TC/		US 6,365,467	B1	04-02-2002	Joo
		US			

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Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Translation <sup>6</sup>
		Country Code <sup>3</sup>	Number <sup>4</sup>			
/TC/		JP	2002-60944	A 02-28-2002	Internat'l Business Mach Corp	
/TC/		JP	10-242461	A 09-11-1998	Sony Corp	
/TC/		JP	2002-164343	A 06-07-2002	Agere Systems Guardian Corp	
/TC/		JP	2002-299607	A 10-11-2002	Toshiba Corp	
/TC/		JP	2001-358225	A 12-26-2001	Agere Systems Guardian Corp	
/TC/		JP	2001-85427	A 03-30-2001	NEC Corp	
/TC/		JP	2001-257344	A 09-21-2001	Toshiba Corp	
/TC/		JP	2001-332547	A 11-30-2001	Toshiba Corp	
/TC/		JP	11-261067	A 09-24-1999	Texas Instr Inc	

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/TC/		Hag-Ju Cho, et al.; "Structural and Electrical Properties of HfO <sub>2</sub> With Top Nitrogen Incorporated Layer"; IEEE Electron Device Letters; Vol. 23 No. 5, May 2002; pages 249-251.			
/TC/		M. Koyama, et al.; "Thermally Stable Ultra-Thin Nitrogen Incorporated ZrO <sub>2</sub> Gate Dielectric Prepared by Low Temperature Oxidation of ZrN"; Tech. Dig. IEDM 2001; pages 459-462.			

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/TC/		JP	2002-299607	A 10-11-2002	Toshiba Corp.	ABS
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/TC/		JP	H10-242461	A 09-11-1998	Sony Corp.	ABS
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/TC/		JP	H11-261067	A 09-24-1999	Texas Instruments Inc.	ABS
/TC/		JP	2002-060944	A 02-28-2002	IBM Corp.	ABS

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